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TOSHIBA PHOTOCOUPLER GaAIAs IRED & PHOTO-IC

# TLP250(INV)

### TRANSISTOR INVERTER INVERTERS FOR AIR CONDITIONER IGBT GATE DRIVE POWER MOS FET GATE DRIVE

The TOSHIBA TLP250(INV) consists of a GaAlAs light emitting diode and a integrated photodetector. This unit is 8-lead DIP.

TLP250(INV) is suitable for gate driving circuit of IGBT or power MOS FET.

- Input Threshold Current : I<sub>F</sub>=5mA(MAX)
- Supply Current(ICC) : 11mA(MAX)
- Supply Voltage(VCC) : 10~35V
- Output Current(IO) : ±2.0A(MAX)
- Switching Time(tpLH/tpHL) : 0.5µs(MAX)
- Isolation Voltage : 2500Vrms
  - UL Recognized : UL1577,File No.E67349
- Option(D4)
  - $\label{eq:VDE Approved : DIN VDE0884/06.92 Certificate No.76823} Maximum Operating Insulation Voltage : 630V_{PK} \\ Highest Permissible Over Voltage : 4000V_{PK} \\ \end{array}$

## (Note):When a VDE0884 approved type is needed, Please designate the "Option(D4)"

Creepage Distance : 6.4mm(MIN)
Clearance : 6.4mm(MIN)

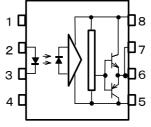
## TRUTH TABLE

	Tr 1	Tr 2	
INPUT LED	ON	ON	OFF
	OFF	OFF	ON

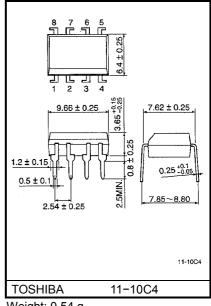
## 

Connected between pin 8 and 5(See Note 5).

### PIN CONFIGURATION(TOP VIEW)



Unit in mm



Weight: 0.54 g

1:N.C. 2: ANODE 3:CATHODE 4:N.C. 5:GND 6:VO(OUTPUT) 7:VO 8:VCC

## MAXIMUM RATINGS (Ta=25°C)

	CHARA	SYMBOL	RATING	UNIT		
	Forward Current	I <sub>F</sub>	20	mA		
	Forward Current Derating (Ta≥	∆l <sub>F</sub> /∆Ta	-0.36	mA /°C		
LED	Peak Transient Forward Currer	I <sub>FPT</sub>	1	А		
	Reverse Voltage	V <sub>R</sub>	5	V		
	Junction Temperature			Tj	125	°C
	"H" Peak	PW ≤2.5µs , f≤15 kH	z	_	-1.5	
	Output Current	PW≤1.0µs , f≤15 kH		I <sub>OPH</sub>	-2.0	A
	"L" Peak	PW≤2.5µs , f≤15 kH	z (Note 2)		+1.5	
	Output Current	PW ≤1.0µs , f≤15 kH	z	I <sub>OPL</sub>	+2.0	A
TOR	Output Valtage	(Ta≤70°C)	M	35	V	
TEC	Output Voltage		(Ta=85°C)	Vo	24	v
DE	Supply Voltage		(Ta≤70°C)	V <sub>cc</sub>	35	v
			(Ta=85°C)	VCC	24	v
	Output Voltage Derating (Ta≥7	0°C)		$\Delta V_{O}$ / $\Delta Ta$	-0.73	V /°C
	Supply Voltage Derating (Ta≥7	$\Delta V_{CC} / \Delta Ta$	-0.73	V /°C		
	Junction Temperature	Tj	125	°C		
Оре	erating Frequency	f	25	kHz		
Оре	erating Temperature Range	T <sub>opr</sub>	-20~85	°C		
Stor	age Temperature Range	T <sub>stg</sub>	-55~125	°C		
Lea	d Soldering Temperature(10s)	T <sub>sol</sub>	260	°C		
Isola	ation Voltage (AC, 1min., R.H.	BVs	2500	Vrms		

(Note 1) : Pulse width PW≤1µs,300pps

(Note 2) : Exporenential Waveform

(Note 3) : Exporenential Waveform  $I_{OPH} \le -1.0A (\le 2.5\mu s)$ ,  $I_{OPL} \le +1.0A (\le 2.5\mu s)$ 

(Note 4) : Device considerd a two terminal device : pins 1,2,3 and 4 shorted together and pins 5,6,7 and 8 shorted together.

(Note 5) : A ceramic capacitor(0.1µF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier.Failure to provide the bypassing may impair the switching proparty.The total lead length between capacitor and coupler should not exceed 1cm.

## **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	YMBOL MIN TYP.		MAX		UNIT
Input Current, ON	I <sub>F (ON)</sub>	7	8	10		mA
Input Voltage, OFF	$V_{F(OFF)}$	0	_	0.8		V
Supply Voltage	V <sub>cc</sub>	15	_	30	20	V
Peak Output Current	I <sub>OPH</sub> / I <sub>OPL</sub>	_	_	±0.5		А
Operating Temperature	T <sub>opr</sub>	-20	25	70	85	°C

## ELECTRICAL CHARACTERISTICS (Ta = -20~70°C,Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Input Forward Voltage		V <sub>F</sub>		I <sub>F</sub> = 10 mA, Ta = 25°C			1.6	1.8	V	
Temperature Coefficier Forward Voltage	nt of	ΔV <sub>F</sub> /ΔTa	_	I <sub>F</sub> = 10 mA				-2.0		mV /°C
Input Reverse Current		I <sub>R</sub>	_	V <sub>R</sub> = 5 V, Ta = 25°C		_	_	10	μA	
Input Capacitance		Ст	_	V = 0, f = 1 MHz, Ta = 25°C			45	250	pF	
Output Current	"H" Level	I <sub>ОРН</sub>	2	V <sub>CC</sub> = 30 V	V	I <sub>F</sub> = 10 mA V <sub>8-6</sub> = 4 V	-1.0	-1.5	_	Α
	"L" Level	I <sub>OPL</sub>	1	(*1)		I <sub>F</sub> = 0 V <sub>6-5</sub> = 2.5 V	1.0	2	_	
Output Voltage	"H" Level	V <sub>он</sub>	3	$\begin{split} & V_{CC1} = +15 \ V \\ & V_{EE1} = -15 \ V \\ & R_L = 200\Omega, \ I_F = 5 \ mA \\ & V_{CC1} = +15 \ V \\ & V_{EE1} = -15 \ V \\ & R_L = 200\Omega, \ V_F = 0.8 \ V \end{split}$		11	12.8	_	v	
Output Voltage	"L" Level	V <sub>OL</sub>	4			_	-14.2	-12.5		
	"H" Level	І <sub>ссн</sub>	_	- V <sub>CC</sub> = 30 V		= 10 mA = 25°C		7		mA
Supply Current					<sub>F</sub> =	= 10 mA			11	
Supply Sullent	"L" Level	I <sub>CCL</sub>	_		l <sub>F</sub> = 0 mA Ta = 25°C			7.5		mA
					۱ <sub>F</sub> =	= 0 mA	_	_	11	
Threshold Input Current	L→H	I <sub>FLH</sub>		$V_{CC1} = +15 V$ $V_{EE1} = -15 V$ $R_L = 200\Omega, V_O > 0V$		_	1.2	5	mA	
Threshold Input Voltage	H→L	V <sub>FHL</sub>		$V_{CC1} = +15 V$ $V_{EE1} = -15 V$ $R_L = 200\Omega, V_O < 0V$		0.8	_	_	V	
Supply Voltage		V <sub>cc</sub>	—			10	_	35	V	
Capacitance (Input-Output)		Cs	—	V <sub>S</sub> = 0, f = 1 MHz, Ta = 25°C		_	1.0	2.0	pF	
Resistance (Input-Output)		Rs	—	V <sub>S</sub> = 500 V, Ta = 25°C R.H.≤60%		1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω	

(\*) : All typical values are at Ta=25°C

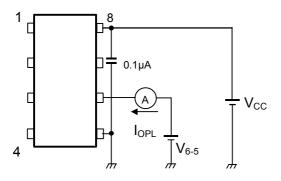
(\*1) : Duration of IO time  $\leq$  50µs

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## SWITCHING CHARACTERISTICS (Ta = -20~70°C,Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Propagation	L→H	t <sub>pLH</sub>			0.05	0.15	0.5	
Delay Time	H→L	t <sub>pHL</sub>		l⊧ = 8 mA.	0.05	0.15	0.5	
Switching Time Dispersion between ON and OFF Output Rise Time Output Fall Time		tpHL-tpLH	5	$V_{cc} = 15 V$ $R_1 = 20\Omega, C_1 = 10nF$	Ι	_	0.45	μs
		tr		$N_{\rm L} = 2032, 0_{\rm L} = 1000$			_	
		t <sub>f</sub>			_		_	
Common Mode Transient Immunity at High Level Output		CM <sub>H</sub>	6	V <sub>CM</sub> = 1000 V, I <sub>F</sub> = 8 mA V <sub>CC</sub> = 30 V, Ta = 25°C	-15000	_	_	V /µs
Common Mode Transient Immunity at Low Level Output		CM∟	0	V <sub>CM</sub> = 1000 V, I <sub>F</sub> = 0 mA V <sub>CC</sub> = 30 V, Ta = 25°C	15000	_	_	V /µs

Fig.1 I<sub>OPL</sub> TEST CIRCUIT



## Fig.2 IOPH TEST CIRCUIT

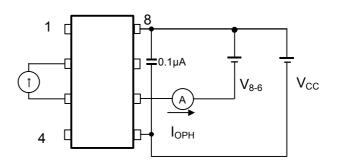
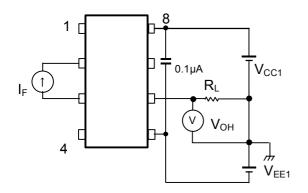
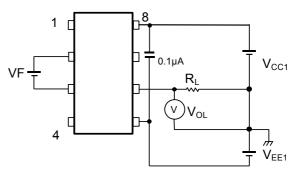


Fig.3 V<sub>OH</sub> TEST CIRCUIT

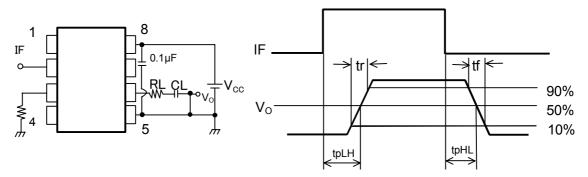


## Fig.4 Vol TEST CIRCUIT

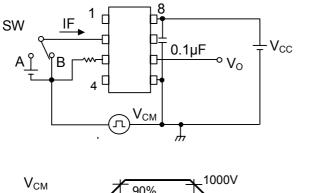


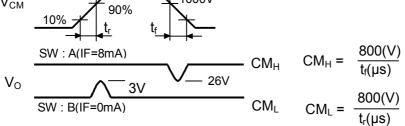
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Fig.5 tpLH、tpHL、tr、tf TEST CIRCUIT



## Fig.6 CM<sub>H</sub>, CM<sub>L</sub> TEST CIRCUIT





CML(CMH) is the maximum rate of rise(fall) of the common mode voltage that can be sustained with the output voltage in the low(high)state.

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